PIN DESCRIPTION

	PIN	NIAME	FUNCTION						
PDIP	PowerCap	NAME	FUNCTION						
1	1	INTB (INTB)	Active-Low Interrupt B, Output, Push-Pull						
2	3	A16							
3	32	A14							
4	30	A12							
5	25	A7							
6	24	A6							
7	23	A5							
8	22	A4							
9	21	A3							
10	20	A2	Address Input						
11	19	A1							
12	18	A0							
23	28	A10							
25	29	A11							
26	27	A9							
27	26	A8							
28	31	A13							
31	2	A15							
13	16	DQ0							
14	15	DQ1							
15	14	DQ2							
17	13	DQ3	Data Input/Output						
18 19	12	DQ4							
20	10	DQ5							
21	9	DQ6 DQ7							
16	17	GND	Ground						
22	8	CE	Active-Low Chip Enable						
24	7	$\overline{\text{OE}}$	Active-Low Output Enable						
29	6	WE	Active-Low Write Enable						
30	_	ĪNTA/SQW	Active-Low, Interrupt A, Open-Drain Output and Square-Wave Output, Shared. Note: Both functions must not be enabled at the same time, or a conflict could occur.						
32	5	V_{CC}	Power-Supply Input						
_	4	PFO	Active-Low Power-Fail Output, Open Drain. Requires a pullup resistor for proper operation.						
_	33	SQW	Square-Wave Output						
_	34	ĪNTA	Active-Low Interrupt A, Output, Open Drain. Requires a pullup resistor for proper operation.						
_		$X1, X2, V_{BAT}$	Crystal Connections and Battery Connection						

DESCRIPTION

The DS1486 is a nonvolatile static RAM with a full-function real-time clock (RTC), alarm, watchdog timer, and interval timer, which are all accessible in a byte-wide format. The DS1486 contains a lithium energy source and a quartz crystal, which eliminate the need for any external circuitry. Data contained within 128K by 8-bit memory and the timekeeping registers can be read or written in the same manner as byte-wide static RAM. The timekeeping registers are located in the first 14 bytes of memory space. Data is maintained in the RAMified timekeeper by intelligent control circuitry, which detects the status of V_{CC} and write-protects memory when V_{CC} is out of tolerance. The lithium energy source can maintain data and real time for over 10 years in the absence of V_{CC}. Timekeeper information includes hundredths of seconds, seconds, minutes, hours, day, date, month, and year. The date at the end of the month is automatically adjusted for months with fewer than 31 days, including correction for leap year. The RAMified timekeeper operates in either 24-hour or 12-hour format with an AM/PM indicator. The watchdog timer provides alarm interrupts and interval timing between 0.01 seconds and 99.99 seconds. The real time alarm provides for preset times of up to one week. Interrupts for both watchdog and RTC will operate when the system is powered down. Either can provide system "wake-up" signals.

PACKAGES

The DS1486 is available in two packages: a 32-pin DIP module and 34-pin PowerCap module. The 32-pin DIP-style module integrates the crystal, lithium energy source, and silicon all in one package. The 32-pin PowerCap Module Board is designed with contacts for connection to a separate PowerCap (DS90934PCX) that contains the crystal and battery. The design allows the PowerCap to be mounted on top of the DS1486P after the completion of the surface mount process. Mounting the PowerCap after the surface mount process prevents damage to the crystal and battery due to high temperatures required for solder reflow. The PowerCap is keyed to prevent reverse insertion. The PowerCap Module Board and PowerCap are ordered separately and shipped in separate containers. The part number for the PowerCap is DS9034PCX.

Table 1. Truth Table

V _{CC}	CE	ŌĒ	WE	MODE	DQ	POWER
	$V_{ m IH}$	X	X	Deselect	High-Z	Standby
	X	X	X	Deselect High-		Standby
5V ±10%	$V_{ m IL}$	X	$V_{ m IL}$	Write	Data In	Active
	$V_{ m IL}$	$V_{ m IL}$	$V_{ m IH}$	Read	Data Out	Active
	$V_{ m IL}$	$V_{ m IH}$	$V_{ m IH}$	Read	High-Z	Active
$\langle 4.5 \text{V} \rangle \text{V}_{\text{BAT}}$	X	X	X	Deselect	High-Z	CMOS Standby
<v<sub>BAT</v<sub>	X	X	X	Deselect	High-Z	Data Retention Mode

OPERATION—READ REGISTERS

The DS1486 executes a read cycle whenever \overline{WE} (Write Enable) is inactive (High), \overline{CE} (Chip Enable) and \overline{OE} (Output Enable) are active (Low). The unique address specified by the address inputs (A0–A16) defines which of the registers is to be accessed. Valid data will be available to the eight data output drivers within t_{ACC} (Access Time) after the last address input signal is stable, providing that \overline{CE} and \overline{OE} access times are also satisfied. If \overline{OE} and \overline{CE} access times are not satisfied, then data access must be measured from the latter occurring signal (\overline{CE} or \overline{OE}) and the limiting parameter is either t_{CO} for \overline{CE} or t_{OE} for \overline{OE} rather than address access.

OPERATION—WRITE REGISTERS

The DS1486 is in the write mode whenever the \overline{WE} (Write Enable) and \overline{CE} (Chip Enable) signals are in the active (Low) state after the address inputs are stable. The latter occurring falling edge of \overline{CE} or \overline{WE} will determine the start of the write cycle. The write cycle is terminated by the earlier rising edge of \overline{CE} or \overline{WE} . All address inputs must be kept valid throughout the write cycle. \overline{WE} must return to the high state for a minimum recovery state (t_{WR}) before another cycle can be initiated. Data must be valid on the data bus with sufficient Data Set-Up (t_{DS}) and Data Hold Time (t_{DH}) with respect to the earlier rising edge of \overline{CE} or \overline{WE} . The \overline{OE} control signal should be kept inactive (High) during write cycles to avoid bus contention. However, if the output bus has been enabled (\overline{CE} and \overline{OE} active), then \overline{WE} will disable the outputs in t_{ODW} from its falling edge.

DATA RETENTION

The RAMified Timekeeper provides full functional capability when V_{CC} is greater than 4.5V. When V_{CC} falls below the power fail trip-point (V_{TP}), the internal \overline{CE} signal is forced high, blocking access (Write-Protect). While in the data retention mode, all inputs are "don't cares," SQW and DQ0–DQ7 go to a high-impedance state. The two interrupts \overline{INTA} and \overline{INTB} (INTB) and the internal clock and timers continue to run regardless of the level of V_{CC} . However, it is important to insure that the pull-up resistors used with the interrupt pins are never pulled up to a value that is greater than $V_{CC}+0.3V$. As V_{CC} falls below approximately 3.0V, a power switching circuit turns the internal lithium energy source on to maintain the clock and timer data functionality. It is also required to ensure that during this time (battery-backup mode), that the voltage present at \overline{INTA} and \overline{INTB} (INTB) never exceeds V_{BAT} . During power-up, when V_{CC} rises above V_{BAT} , the power-switching circuit connects external V_{CC} and disconnects the internal lithium energy source. Normal operation can resume after V_{CC} exceeds 4.5V for a period of 200ms.

RAMIFIED TIMEKEEPER REGISTERS

The RAMified timekeeper has 14 registers that are 8 bits wide that contain all the timekeeping, alarm, watchdog, and control information. The clock, calendar, alarm, and watchdog registers are memory locations that contain external (user-accessible) and internal copies of the data. The external copies are independent of internal functions, except that they are updated periodically by the simultaneous transfer of the incremented internal copy (see Figure 1). The Command Register bits are affected by both internal and external functions. This register will be discussed later. Registers 0, 1, 2, 4, 6, 8, 9, and A contain time-of-day and date information (see Figure 2). Time-of-day information is stored in BCD. Registers 3, 5, and 7 contain the Time-of-Day Alarm information. Time-of-Day Alarm information is stored in BCD. Register B is the Command Register and information in this register is binary. Registers C and D are the Watchdog Alarm Registers and information that is stored in these two registers is in BCD. Registers E through 1FFFF are user bytes and can be used to maintain data at the user's discretion.

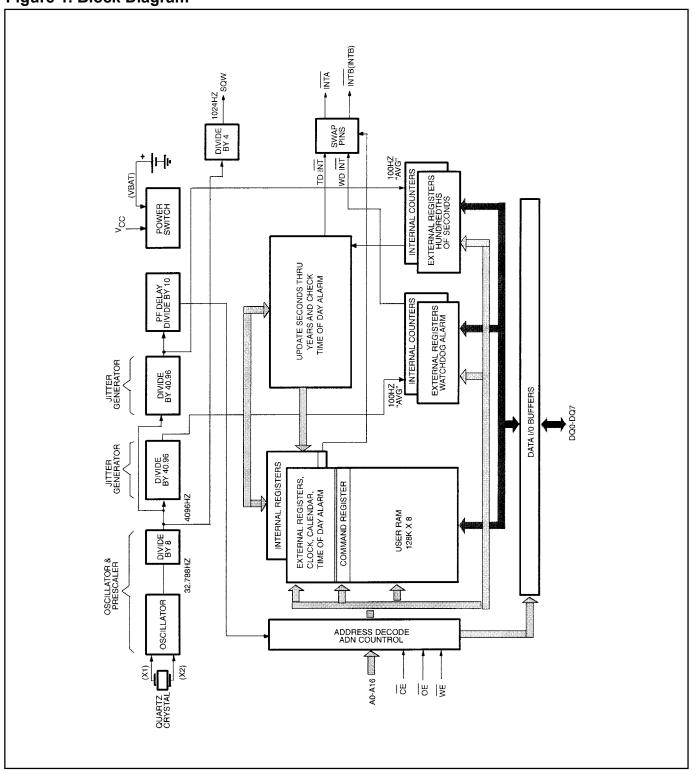
CLOCK ACCURACY (DIP MODULE)

The DS1486 is guaranteed to keep time accuracy to within ±1 minute per month at +25°C.

CLOCK ACCURACY (PowerCap MODULE)

The DS1486P and DS9034PCX are each individually tested for accuracy. Once mounted together, the module is guaranteed to keep time accuracy to within ± 1.53 minutes per month (35ppm) at ± 25 °C.

Figure 1. Block Diagram



TIME-OF-DAY REGISTERS

Registers 0, 1, 2, 4, 6, 8, 9, and A contain Time-of-Day data in BCD. Ten bits within these eight registers are not used and will always read 0 regardless of how they are written. Bits 6 and 7 in the Months Register (9) are binary bits. When set to logic 0, EOSC (Bit 7) enables the real-time clock oscillator. This bit is set to logic 1 as shipped from Dallas Semiconductor to prevent lithium energy consumption during storage and shipment (DIP Module only). This bit will normally be turned on by the user during device initialization. However, the oscillator can be turned on and off as necessary by setting this bit to the appropriate level. The INTA and Square Wave Output signals are tied together at pin 30 on the 32-pin DIP module. With this package, ESQW (Bit 6) of the Months Register (9) controls the function of this pin. When set to logic 0, the pin will output a 1024 Hz square wave signal. When set to logic 1, the pin is available for interrupt A output (INTA) only. The INTA and Square Wave Output signals are separated on the 34-pin PowerCap module. With this package, ESQW controls only the Square Wave Output (pin 33). When set to logic 0, pin 33 will output a 1024 Hz square wave signal. When set to logic 1, pin 33 is in a high impedance state. Pin 34 (INTA) is not affected by the setting of bit 6. Bit 6 of the Hours register is defined as the 12- or 24-hour select bit. When set to logic 1, the 12-hour format is selected. In the 12hour format, bit 5 is the AM/PM bit with logic 1 being PM. In the 24-hour mode, bit 5 is the second 10hour bit (20-23 hours). The Time-of-Day registers are updated every 0.01 seconds from the real-time clock, except when the TE bit (bit 7 of Register B) is set low or the clock oscillator is not running. The preferred method of synchronizing data access to and from the RAMified Timekeeper is to access the Command register by doing a write cycle to address location B and setting the TE bit (Transfer Enable bit) to a logic 0. This will freeze the External Time-of-Day registers at the present recorded time, allowing access to occur without danger of simultaneous update. When the watch registers have been read or written, a second write cycle to location B setting the TE bit to a logic 1 will put the Time-of-Day Registers back to being updated every 0.01 second. No time is lost in the real-time clock because the internal copy of the Time-of-Day register buffers is continually incremented while the external memory registers are frozen. An alternate method of reading and writing the Time-of-Day registers is to ignore synchronization. However, any single reading may give erroneous data as the real-time clock may be in the process of updating the external memory registers as data is being read. The internal copies of seconds through years are incremented and the Time-of-Day Alarm is checked during the period that hundreds of seconds reads 99. The copies are transferred to the external register when hundredths of seconds roll from 99 to 00. A way of making sure data is valid is to do multiple reads and compare. Writing the registers can also produce erroneous results for the same reasons. A way of making sure that the write cycle has caused a proper update is to perform read verifies and re-execute the write cycle if data is not correct. While the possibility of erroneous results from read and write cycles has been stated, it is worth noting that the probability of an incorrect result is kept to a minimum due to the redundant structure of the RAMified Timekeeper.

TIME-OF-DAY ALARM REGISTERS

Registers 3, 5, and 7 contain the Time-of-Day Alarm Registers. Bits 3, 4, 5, and 6 of Register 7 will always read 0 regardless of how they are written. Bit 7 of Registers 3, 5, and 7 are mask bits (Figure 3). When all of the mask bits are logic 0, a Time-of-Day Alarm will only occur when Registers 2, 4, and 6 match the values stored in Registers 3, 5, and 7. An alarm will be generated every day when bit 7 of Register 7 is set to a logic 1. Similarly, an alarm is generated every hour when bit 7 of Registers 7 and 5 is set to a logic 1. When bit 7 of Registers 7, 5, and 3 is set to a logic 1, an alarm will occur every minute when Register 1 (seconds) rolls from 59 to 00.

Time-of-Day Alarm Registers are written and read in the same format as the Time-of-Day Registers. The Time-of-Day Alarm Flag and Interrupt are always cleared when Alarm Registers are read or written.

WATCHDOG ALARM REGISTERS

Registers C and D contain the time for the Watchdog Alarm. The two registers contain a time count from 00.01 to 99.99 seconds in BCD. The value written into the Watchdog Alarm Registers can be written or read in any order. Any access to Register C or D will cause the Watchdog Alarm to reinitialize and clears the Watchdog Flag bit and the Watchdog Interrupt Output. When a new value is entered or the Watchdog Registers are read, the Watchdog Timer will start counting down from the entered value to 0. When 0 is reached, the Watchdog Interrupt Output will go to the active state. The Watchdog Timer Countdown is interrupted and reinitialized back to the entered value every time either of the registers is accessed. In this manner, controlled periodic accesses to the Watchdog Timer can prevent the Watchdog Alarm from going to an active level. If access does not occur, countdown alarm will be repetitive. The Watchdog Alarm Registers always read the entered value. The actual countdown register is internal and is not readable. Writing registers C and D to 0 will disable the Watchdog Alarm feature.

Figure 2. RAMified Timekeeper Registers

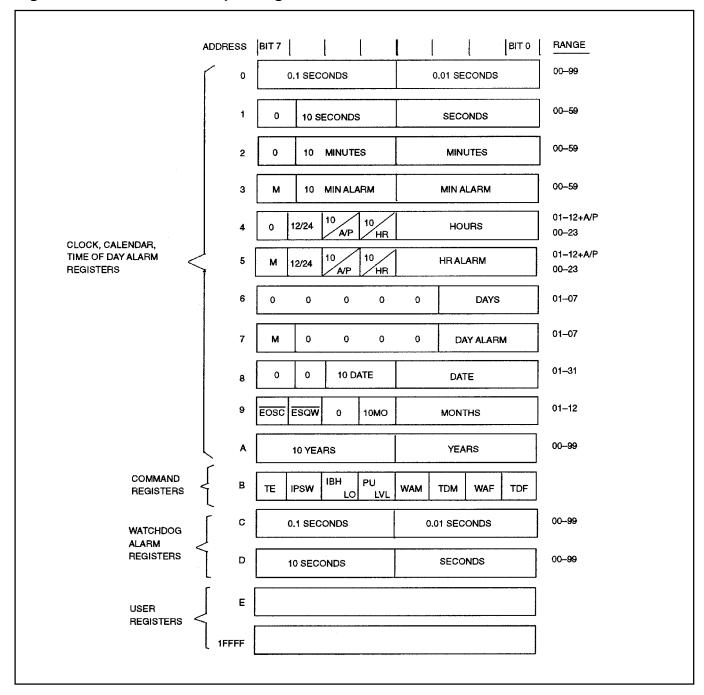


Figure 3. Time-of-Day Alarm Mask Bits

	REGISTER		ALARM RATE		
(3) MINUTES	(5) HOURS	(7) DAYS			
1	1	1	Alarm once per minute		
0	1	1	Alarm when minutes match		
0	0	1	Alarm when hours and minutes match		
0	0	0	Alarm when hours, minutes, and days match		

Note: Any other bit combinations of mask bit settings produce illogical operation.

COMMAND REGISTER (0Bh)

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
TE	IPSW	IBH/LO	PU/LVL	WAM	TDM	WAF	TDF

- **Bit 7: Transfer Enable (TE).** This bit when set to a logic 0 will disable the transfer of data between internal and external clock registers. The contents in the external clock registers are now frozen and reads or writes will not be affected with updates. This bit must be set to a logic 1 to allow updates.
- **Bit 6: Interrupt Switch (IPSW).** When set to a logic 1, $\overline{\text{INTA}}$ is the Time-of-Day Alarm and $\overline{\text{INTB}}$ (INTB) is the Watchdog Alarm. When set to logic 0, this bit reverses the output pins. $\overline{\text{INTA}}$ is now the Watchdog Alarm output and $\overline{\text{INTB}}$ (INTB) is the Time-of-Day Alarm output. The $\overline{\text{INTA}}$ /SQW output pin shares both the interrupt A and square-wave output function. $\overline{\text{INTA}}$ and the square wave function should never be simultaneously enabled or a conflict may occur (32-pin DIP module only).
- Bit 5: Interrupt B Sink or Source Current (IBH/LO). When this bit is set to a logic 1 and V_{CC} is applied, $\overline{\text{INTB}}$ (INTB) will source current (see DC characteristics IOH). When this bit is set to a logic 0, INTB will sink current (see I_{OL} in the *DC Characteristics*).
- Bit 4: Interrupt Pulse Mode or Level Mode (PU/LVL). This bit determines whether both interrupts will output a pulse or level signal. When set to a logic 0, $\overline{\text{INTA}}$ and $\overline{\text{INTB}}$ (INTB) will be in the level mode. When this bit is set to a logic 1, the pulse mode is selected and $\overline{\text{INTA}}$ will sink current for a minimum of 3ms and then release. $\overline{\text{INTB}}$ (INTB) will either sink or source current, depending on the condition of Bit 5, for a minimum of 3ms and then release. INTB will only source current when there is a voltage present on V_{CC} .
- **Bit 3: Watchdog Alarm Mask (WAM).** When this bit is set to a logic 0, the Watchdog Interrupt output will be activated. The activated state is determined by bits 1, 4, 5, and 6 of the Command Register. When this bit is set to a logic 1, the Watchdog interrupt output is deactivated.
- **Bit 2: Time-of-Day Alarm Mask (TDM).** When this bit is set to a logic 0, the Time-of-Day Alarm Interrupt output will be activated. The activated state is determined by bits 0, 4, 5, and 6 of the Command Register. When this bit is set to a logic 1, the Time-of-Day Alarm interrupt output is deactivated.
- **Bit 1:** Watchdog Alarm Flag (WAF). This bit is set to a logic 1 when a watchdog alarm interrupt occurs. This bit is read only. The bit is reset when any of the Watchdog Alarm registers are accessed.

When the interrupt is in the pulse mode (see bit 4 definition), this flag will be in the logic 1 state only during the time the interrupt is active.

Bit 0: Time-of-Day Flag (TDF). This is a read-only bit. This bit is set to a logic 1 when a Time-of-Day alarm has occurred. The time the alarm occurred can be determined by reading the Time-of-Day Alarm registers. This bit is reset to a logic 0 state when any of the Time-of-Day Alarm registers are accessed.

When the interrupt is in the pulse mode (see bit 4 definition), this flag will be in the logic 1 state only during the time the interrupt is active.

ABSOLUTE MAXIMUM RATINGS

Voltage Range on Any Pin Relative to Ground	0.3V to +6.0V
Operating Temperature Range (Noncondensing)	0°C to +70°C
Storage Temperature Range	40°C to +85°C
Soldering Temperature (EDIP) (leads, 10 seconds)	+260°C for 10 seconds (Note 14)
Soldering Temperature	See IPC/JEDEC J-STD-020 Specification (Note 14)

This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

 $(T_A = 0^{\circ}C \text{ to } +70^{\circ}C)$

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Power-Supply Voltage	V_{CC}	4.5	5.0	5.5	V	10
Input Logic 1	$V_{ m IH}$	2.2		V _{CC} + 0.3	V	10
Input Logic 0	$V_{ m IL}$	-0.3		+0.8	V	10

DC ELECTRICAL CHARACTERISTICS

 $(V_{CC} = 5V \pm 10\%, T_A = 0^{\circ}C \text{ to } +70^{\circ}C.)$

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Leakage Current	I_{IL}	-1.0		+1.0	μΑ	
Output Leakage Current	I_{LO}	-1.0		+1.0	μΑ	
I/O Leakage Current	I _{LIO}	-1.0		+1.0	μΑ	
Output Current at 2.4V	I _{OH}	-1.0			mA	13
Output Current at 0.4V	I_{OL}			2.1	mA	13
Standby Current $\overline{CE} = 2.2V$	I _{CCS1}		3.0	7.0	mA	
Standby Current $\overline{\text{CE}} = V_{\text{CC}} - 0.5$	I _{CCS2}			4.0	mA	
Active Current	I_{CC}			85	mA	
Write Protection Voltage	V_{TP}	4.0	4.25	4.5	V	

CAPACITANCE

 $(T_A = +25^{\circ}C)$

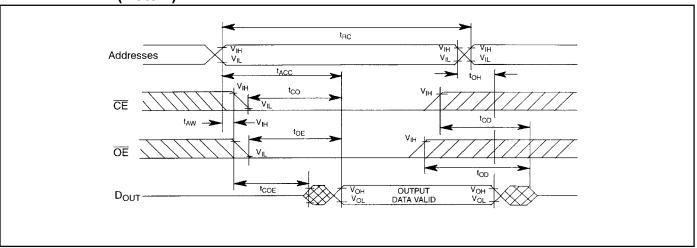
(·A =0 0)						
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Capacitance	C_{IN}		7	15	pF	
Output Capacitance	C _{OUT}		7	15	pF	
Input/Output Capacitance	C _{I/O}		7	15	рF	

AC ELECTRICAL CHARACTERISTICS

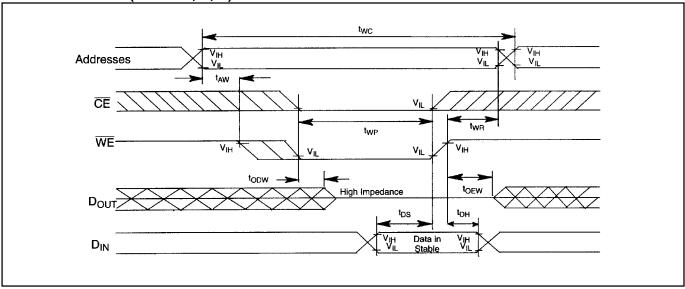
 $(V_{CC} = 5.0V \pm 10\%, T_A = 0^{\circ}C \text{ to } +70^{\circ}C.)$

PARAMETER	SYMBOL	MIN	MAX	UNITS	NOTES
Read Cycle Time	t_{RC}	120		ns	1
Address Access Time	t_{ACC}		120	ns	
CE Access Time	t_{CO}		120	ns	
OE Access Time	$t_{ m OE}$		100	ns	
OE or CE to Output Active	$t_{\rm COE}$	10		ns	
Output High-Z from Deselect	t_{OD}		40	ns	
Output Hold from Address Change	t_{OH}	10		ns	
Write Cycle Time	$t_{ m WC}$	120		ns	
Write Pulse Width	t_{WP}	110		ns	3
Address Setup Time	$t_{ m AW}$	0		ns	
Write Recovery Time	$t_{ m WR}$	10		ns	
Output High-Z from WE	$t_{ m ODW}$		40	ns	
Output Active from WE	t_{OEW}	10		ns	4
Data Setup Time	$t_{ m DS}$	85		ns	4
Data Hold Time	t _{DH}	10		ns	4, 5
INTA, INTB Pulse Width	$t_{ m IPW}$	3	·	ms	11, 12

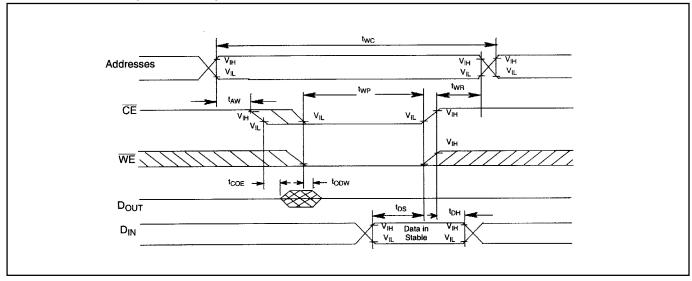
READ CYCLE (Note 1)



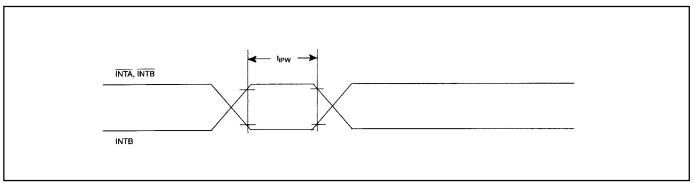
WRITE CYCLE 1 (Notes 2, 6, 7)



WRITE CYCLE 2 (Notes 2, 8)



TIMING DIAGRAM: INTERRUPT OUTPUTS PULSE MODE (Notes 11, 12)

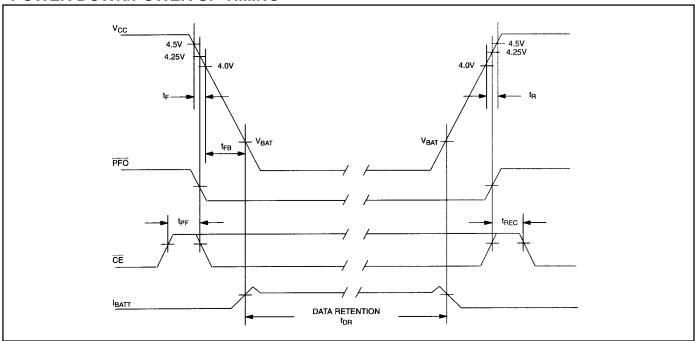


POWER-UP/POWER-DOWN TIMING

 $(T_A = 0^{\circ}C \text{ to } +70^{\circ}C)$

PARAMETER	SYMBOL	MIN	MAX	UNITS	NOTES
CE High to Power-Fail	$t_{ m PF}$		0	ns	
Recovery at Power-Up	$t_{ m REC}$		200	ms	
V _{CC} Slew Rate Power-Down	t_{F} $4.0 \le V_{CC} \le 4.5V$	300		μs	
V _{CC} Slew Rate Power-Down	t_{FB} $3.0 \le V_{CC} \le 4.25V$	10		μs	
V _{CC} Slew Rate Power-Up	t_{R} $4.5V \ge V_{CC} \ge 4.0V$	0		μs	
Expected Data Retention	t_{DR}	10		years	9

POWER-DOWN/POWER-UP TIMING



WARNING:

Under no circumstances are negative undershoots, of any amplitude, allowed when device is in battery-backup mode.

NOTES:

- 1) $\overline{\text{WE}}$ is high for a read cycle.
- 2) $\overline{OE} = V_{IH}$ or V_{IL} . If $\overline{OE} = V_{IH}$ during write cycle, the output buffers remain in a high-impedance state.
- 3) t_{WP} is specified as the logical AND of the \overline{CE} and \overline{WE} . t_{WP} is measured from the latter of \overline{CE} or \overline{WE} going low to the earlier of \overline{CE} or \overline{WE} going high.
- 4) t_{DS} or t_{DH} are measured from the earlier of \overline{CE} or \overline{WE} going high.
- 5) t_{DH} is measured from \overline{WE} going high. If \overline{CE} is used to terminate the write cycle, then $t_{DH} = 20$ ns.
- 6) If the $\overline{\text{CE}}$ low transition occurs simultaneously with or later than the $\overline{\text{WE}}$ low transition in write cycle 1, the output buffers remain in a high-impedance state during this period.
- 7) If the $\overline{\text{CE}}$ high transition occurs prior to or simultaneously with the $\overline{\text{WE}}$ high transition, the output buffers remain in a high impedance state during this period.
- 8) If $\overline{\text{WE}}$ is low or the $\overline{\text{WE}}$ low transition occurs prior to or simultaneously with the $\overline{\text{CE}}$ low transition, the output buffers remain in a high-impedance state during this period.
- 9) Each DS1486 is marked with a four-digit date code AABB. AA designates the year of manufacture. BB designates the week of manufacture. The expected t_{DR} is defined for DIP Modules as starting at the date of manufacture.
- 10) All voltages are referenced to ground.
- 11) Applies to both interrupt pins when the alarms are set to pulse.
- 12) Interrupt output occurs within 100ns on the alarm condition existing.
- 13) Both INTA and INTB (INTB) are open-drain outputs.
- 14) Real-Time Clock Modules (DIP) can be successfully processed through conventional wave-soldering techniques as long as temperature exposure to the lithium energy source contained within does not exceed +85°C. Post-solder cleaning with water washing techniques is acceptable, provided that ultrasonic vibration is not used. See the PowerCap package drawing for details regarding the PowerCap package.

AC TEST CONDITIONS

Output Load: 50pF + 1TTL Gate Input Pulse Levels: 0 to 3.0V

Timing Measurement Reference Levels

Input: 1.5V Output: 1.5V

Input Pulse Rise and Fall Times: 5ns

PACKAGE INFORMATION

For the latest package outline information, go to www.maxim-ic.com/DallasPackInfo.

28-pin 740 EDIP Module Document number: <u>56-G0002-001</u> 32-pin PowerCap Module Document number: <u>56-G0003-001</u>

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